

DSS30101L

LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Features

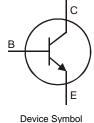
- Ideal for Medium Power Amplification and Switching
- Ultra Low Collector-Emitter Saturation Voltage
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- ESD rating: 400V-MM, 8KV-HBM

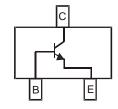
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)









Top View

Pin Configuration

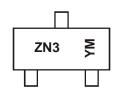
Ordering Information

Part Number	Case	Packaging
DSS30101L-7	SOT-23	3000/Tape & Reel

Notes:

- 1. No purposefully added lead. Halogen and Antimony Free.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



ZN3 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008)M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I _{CM}	2	А
Continuous Collector Current	I _C	1	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P_{D}	600	mW
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	$R_{ heta JA}$	209	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 3. Device mounted on FR-4 PCB MRP

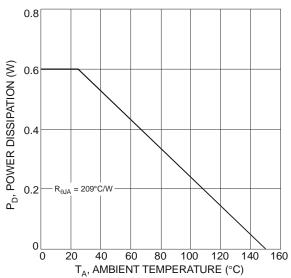


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

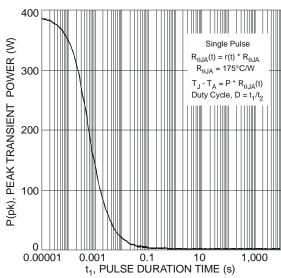
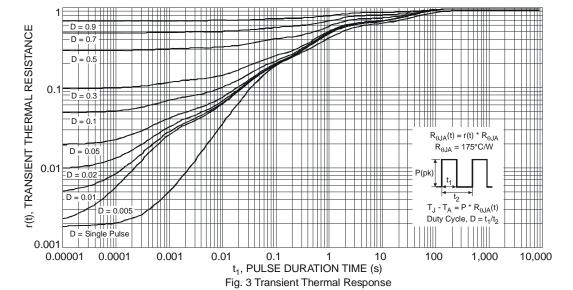


Fig. 2 Single Pulse Maximum Power Dissipation

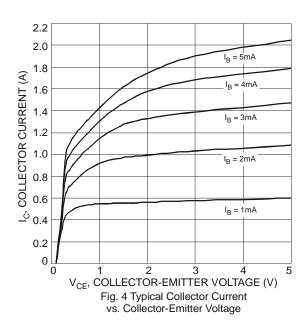


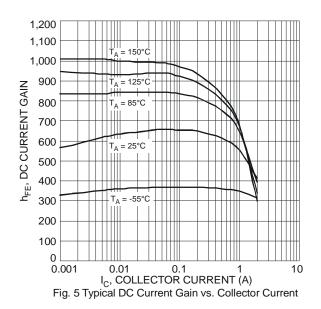


Electrical Characteristics @T_A = 25°C unless otherwise specified

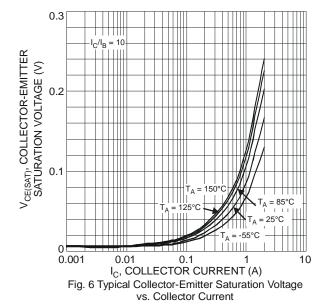
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
Collector-Base Breakdown Voltage	V _{(BR)CBO}	50			V	$I_C = 100 \mu A$	
Collector-Emitter Breakdown Voltage (Note 4)	V _{(BR)CEO}	30	_	_	V	$I_C = 10mA$	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	_		V	$I_E = 100 \mu A$	
Collector-Base Cutoff Current	_			100	nA	$V_{CB} = 30V, I_{E} = 0$	
Collector-Base Cuton Current	I _{CBO}		_	50	μΑ	$V_{CB} = 30V, I_E = 0, T_A = 150^{\circ}C$	
Emitter-Base Cutoff Current	I _{EBO}			100	nA	$V_{EB} = 4V, I_{C} = 0$	
		300	_	_		$V_{CE} = 5V$, $I_C = 50mA$	
DC Current Gain (Note 4)	h _{FE}	300	450	900	_	$V_{CE} = 5V, I_{C} = 0.5A$	
		200				$V_{CE} = 5V$, $I_C = 1A$	
			_	75		$I_C = 0.1A, I_B = 1mA$	
Collector-Emitter Saturation Voltage (Note 4)	V _{CE(sat)}			125	mV	$I_C = 0.5A$, $I_B = 50mA$	
		_	_	200		$I_C = 1.0A$, $I_B = 100mA$	
Equivalent On-Resistance (Note 4)	R _{CE(sat)}	_	_	200	mΩ	I _E = 1A, I _B = 100mA	
Base-Emitter Saturation Voltage (Note 4)	V _{BE(sat)}		0.93	1.1	V	$I_C = 1A$, $I_B = 100mA$	
Base-Emitter Turn-on Voltage (Note 4)	V _{BE(on)}		0.80	1.1	V	$V_{CE} = 2V$, $I_C = 1A$	
Transition Frequency	f _T	100	250	_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz	
Output Capacitance	C_{obo}	_	9	15	pF	V _{CB} = 10V, f = 1MHz	
Input Capacitance	C _{ibo}		65	— .	pF	$V_{EB} = 5V, f = 1MHz$	
Turn-On Time	t _{on}		57	_	ns		
Delay Time	t _d	_	19	_	ns		
Rise Time	t _r	_	38	_	ns	$V_{CC} = 5V$, $I_{C} = 500$ mA,	
Turn-Off Time	t _{off}		340	_	ns	$I_{B1} = -I_{B2} = 50\text{mA}$	
Storage Time	ts		315	_	ns		
Fall Time	t _f	_	25	_	ns		

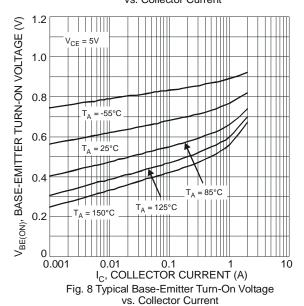
Notes: 4. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.











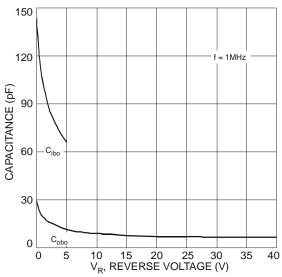
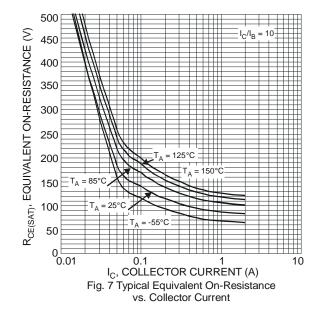
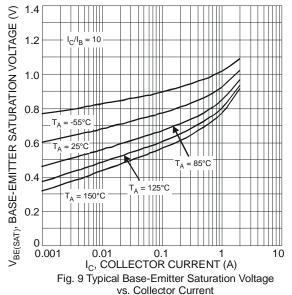


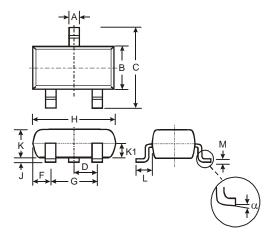
Fig. 10 Typical Capacitance Characteristics





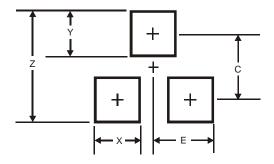


Package Outline Dimensions



SOT-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
M	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
Е	1.35



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